

Proximity Sensor



G18-3A10NAT



G18-3A10NA



G30-3A70NA



G63-3E30NA



G50-134JC



G50-3A30JC



G139-3A/NA



G80-3A80NA



G76-2010JC

Model composition and definition of infrared ray photoelectric sensor

G 18 - 3 A 10 N A □
1 2 3 4 5 6 7 8

No.	Composition	Code and definition
1	Basic form	G:infrared ray photoelectric switch
2	Outward appearance code	18,50,76.....
3	Working voltage	2.90-250VAC 3:10-30VDC 4:12-240VDC/24-240VAC Special voltage
4	Detection way	A:diffused reflection type(scattered reflection type) B:feedback reflection type mirror(mirror reflection type) C:penetration type(correlation typ) D:marking detection type G:optical fibre type
5	Detection distance	05:5cm 10:10cm 3:3cm 101:10m
6	Output form	N:NPN transistor output P:PNPtransistor output J:Relay contact output L:AC two-wire output S:with two outputs:NPN and PNP
7	Output state	A:Normally open (light entering ON) B:Normally closed(light sheltering ON) C:Normally open+normally closed
8	Subsidiary	T1:front delay T2:rear delay T:with aviation connector I:special requirement